

GSMDS3911

30V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

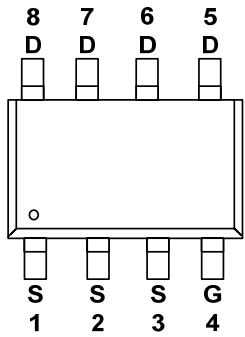
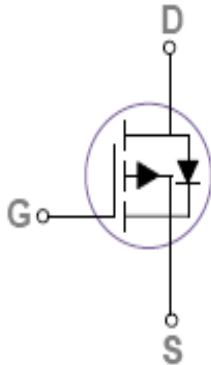
Features

- -30V, -5.5A, $R_{DS(ON)}=50m\Omega@V_{GS}=-10V$
- Fast switching
- Suit for -4.5V Gate Drive Applications
- Green Device Available
- SOP-8 package design

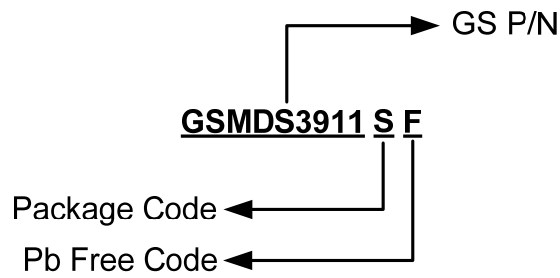
Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-Held Instruments

Packages & Pin Assignments

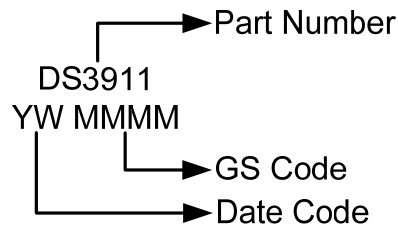
GSMDS3911SF (SOP-8)			
			
			
Pin	Description	Pin	Description
1	Source	5	Drain
2	Source	6	Drain
3	Source	7	Drain
4	Gate	8	Drain

Ordering Information



Part Number	Package	Quantity Reel
GSMD53911SF	SOP-8	4000 PCS

Marking Information



Absolute Maximum Ratings

T_A=25°C Unless otherwise noted

Symbol	Parameter	Typical	Unit
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _A =25°C	-5.5
		T _A =100°C	-3.48
I _{DM}	Pulsed Drain Current	-22	A
P _D	Power Dissipation (T _A =25°C)	2.1	W
	Power Dissipation (Derate above 25°C)	0.017	W/°C
T _J	Operating Junction Temperature Range	-55 to +150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	60	°C/W

Note 1: Repetitive Rating : Pulsed width limited by maximum junction temperature.

Electrical Characteristics

T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA		-0.03		V/°C
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1.0	-1.6	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient			4		mV/°C
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =125°C			-10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			-5.5	A
I _{SM}	Pulsed Source Current				-11	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3A		40	50	mΩ
		V _{GS} =-4.5V, I _D =-2A		62	80	
g _{FS}	Forward Transconductance	V _{DS} =-10V, I _D =-3A		3.5		S
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A			-1	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A		5.1	7	nC
Q _{gs}	Gate-Source Charge			2	3	
Q _{gd}	Gate-Drain Charge			2.2	4	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz		560	810	pF
C _{oss}	Output Capacitance			55	80	
C _{rss}	Reverse Transfer Capacitance			40	60	
t _{d(on)}	Turn-On Time	V _{DD} =-15V, I _D =-1A, V _{GS} =-10V, R _G =6Ω		3.4	6	ns
t _r				10.8	21	
t _{d(off)}	Turn-Off Time			26.9	51	
t _f				6.9	13	

Note 2: The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.

Note 3: Essentially independent of operating temperature.

Typical Performance Characteristics

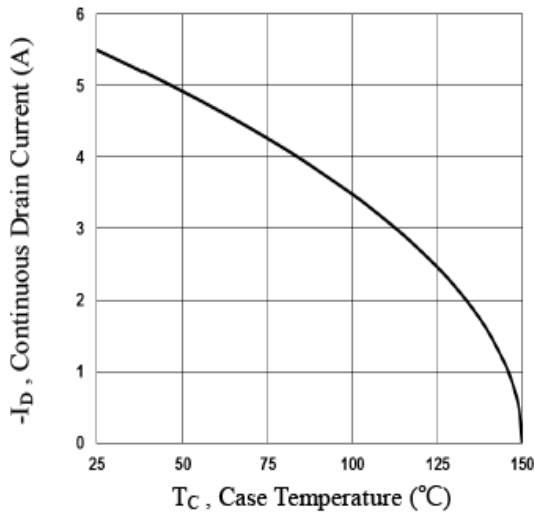


Fig.1 Continuous Drain Current vs. T_C

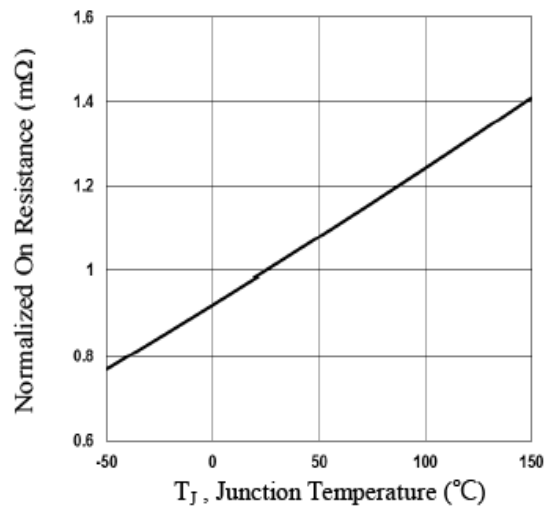


Fig.2 Normalized RDSON vs. T_J

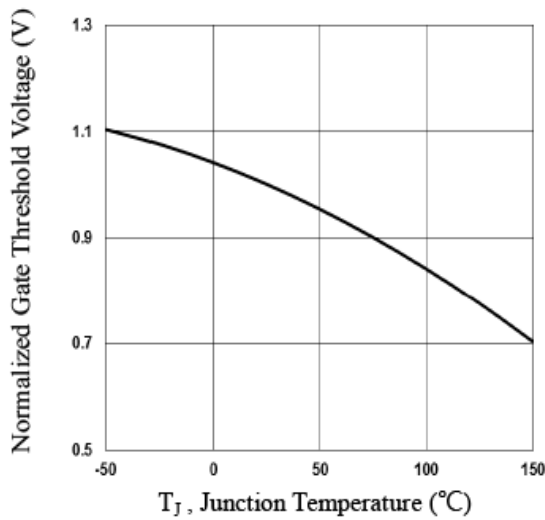


Fig.3 Normalized V_{th} vs. T_J

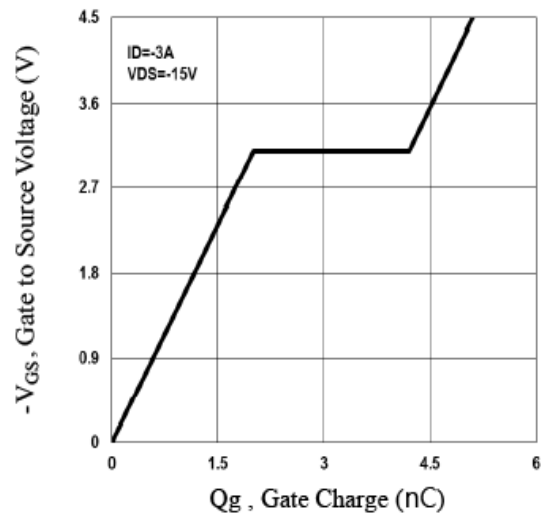


Fig.4 Gate Charge Waveform

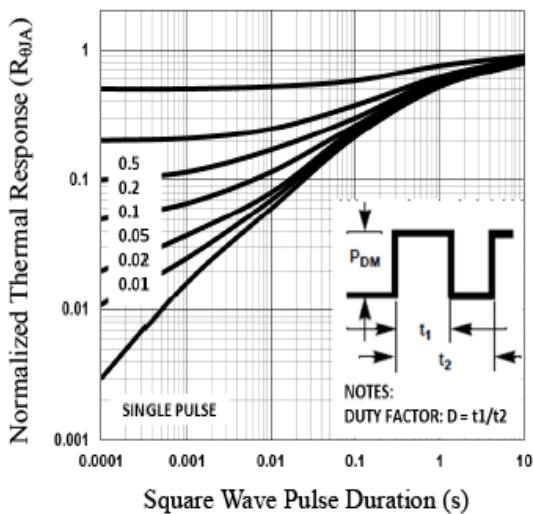


Fig.5 Normalized Transient Impedance

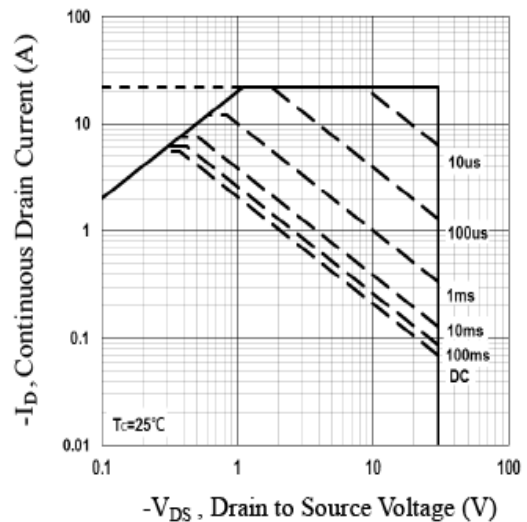
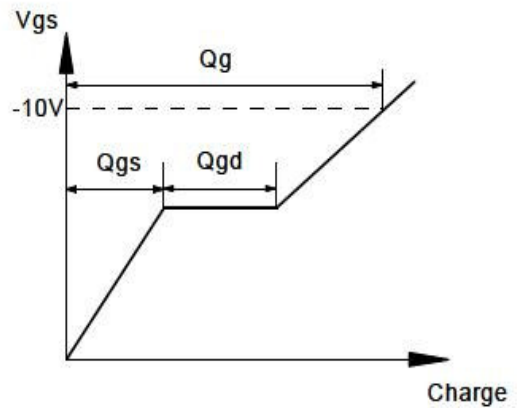
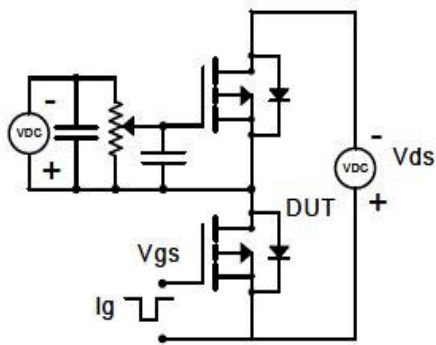


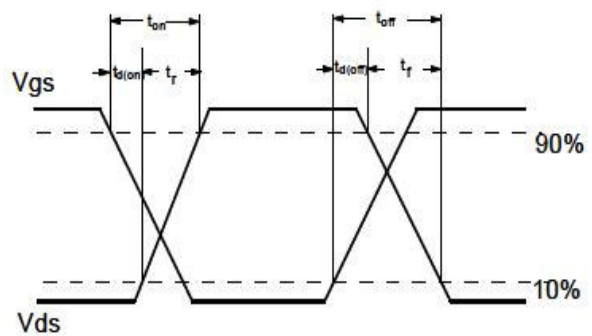
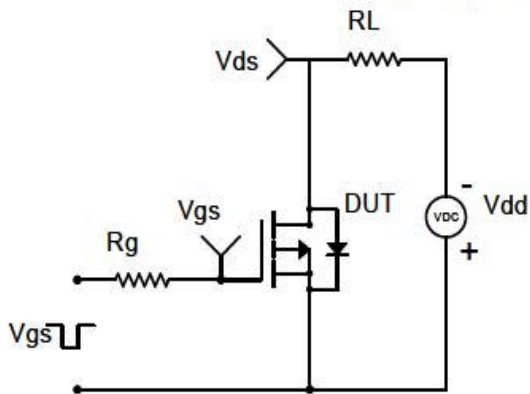
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

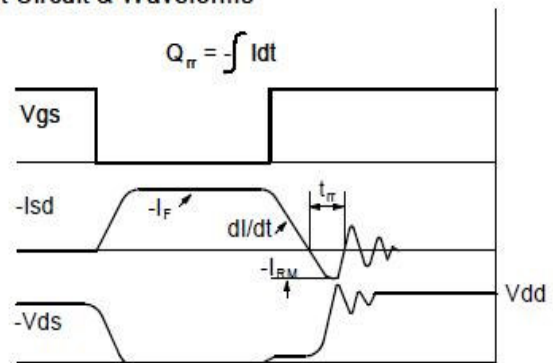
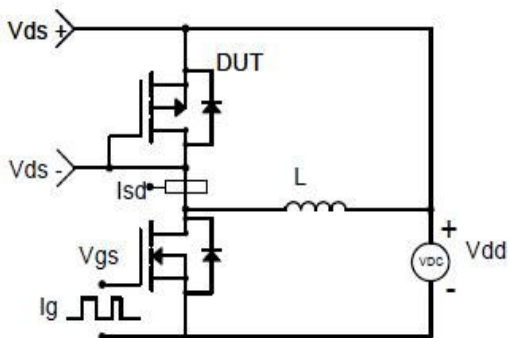
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

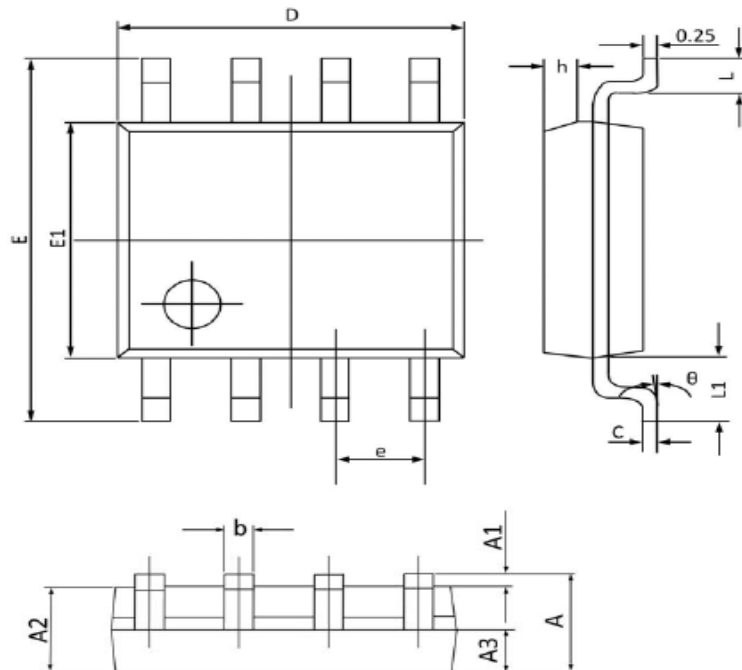


Diode Recovery Test Circuit & Waveforms



Package Dimension

SOP-8







Dimensions




Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270 (BSC)		0.050 (BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050 (BSC)		0.041 (BSC)	
θ	0°	8°	0°	8°



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